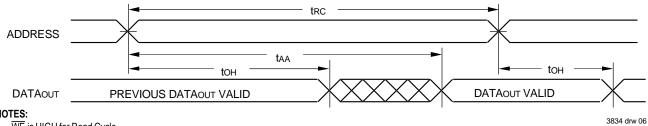
AC Electrical Characteristics (VDD = Min. to Max., Commercial and Industrial Temperature Ranges)

Symbol Parameter	71V016SA10 ⁽²⁾		71V016SA12		71V016SA15		71V016SA20		
	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
<u> </u>	•			•					
Read Cycle Time	10	_	12	_	15		20	_	ns
Address Access Time		10		12		15	_	20	ns
Chip Select Access Time	_	10		12		15	_	20	ns
Chip Select Low to Output in Low-Z	4	_	4	_	5		5	_	ns
Chip Select High to Output in High-Z	_	5		6	_	6	_	8	ns
Output Enable Low to Output Valid	_	5		6	_	7		8	ns
Output Enable Low to Output in Low-Z	0	_	0	_	0		0	_	ns
Output Enable High to Output in High-Z	_	5	_	6	_	6	_	8	ns
Output Hold from Address Change	4	_	4	_	4	_	4	_	ns
Byte Enable Low to Output Valid	_	5	_	6	_	7		8	ns
Byte Enable Low to Output in Low-Z	0	_	0	_	0		0		ns
Byte Enable High to Output in High-Z	_	5	_	6	_	6	_	8	ns
E									
Write Cycle Time	10	_	12	_	15	_	20		ns
Address Valid to End of Write	7	_	8	_	10		12	_	ns
Chip Select Low to End of Write	7		8		10		12		ns
Byte Enable Low to End of Write	7		8		10		12		ns
Address Set-up Time	0		0		0		0		ns
Address Hold from End of Write	0		0	_	0		0		ns
Write Pulse Width	7	_	8	_	10		12		ns
Data Valid to End of Write	5		6		7		9		ns
Data Hold Time	0	_	0		0		0		ns
Write Enable High to Output in Low-Z	3		3		3		3		ns
Write Enable Low to Output in High-Z	_	5	_	6	_	6	_	8	ns
	Read Cycle Time Address Access Time Chip Select Access Time Chip Select Low to Output in Low-Z Chip Select High to Output in High-Z Output Enable Low to Output Valid Output Enable Low to Output in Low-Z Output Enable High to Output in High-Z Output Enable High to Output in High-Z Output Hold from Address Change Byte Enable Low to Output Valid Byte Enable Low to Output in Low-Z Byte Enable High to Output in High-Z E Write Cycle Time Address Valid to End of Write Chip Select Low to End of Write Byte Enable Low to End of Write Address Set-up Time Address Hold from End of Write Write Pulse Width Data Valid to End of Write Data Hold Time Write Enable High to Output in Low-Z	Read Cycle Time 10 Address Access Time —— Chip Select Access Time —— Chip Select Low to Output in Low-Z 4 Chip Select High to Output in High-Z —— Output Enable Low to Output in Low-Z 0 Output Enable High to Output in High-Z —— Output Enable High to Output in High-Z —— Output Enable High to Output in High-Z —— Output Hold from Address Change 4 Byte Enable Low to Output Valid —— Byte Enable Low to Output in Low-Z 0 Byte Enable High to Output in High-Z —— E Write Cycle Time 10 Address Valid to End of Write 7 Chip Select Low to End of Write 7 Byte Enable Low to End of Write 7 Address Set-up Time 0 Address Hold from End of Write 5 Data Hold Time 0 Write Enable High to Output in Low-Z 3	Read Cycle Time 10 — Address Access Time 10 — Chip Select Access Time — 10 Chip Select Low to Output in Low-Z 4 — Chip Select High to Output in High-Z — 5 Output Enable Low to Output in Low-Z 0 — Output Enable High to Output in High-Z — 5 Output Hold from Address Change 4 — Byte Enable Low to Output Valid — 5 Byte Enable Low to Output in Low-Z 0 — Byte Enable Low to Output in Low-Z 0 — Byte Enable High to Output in High-Z 5 E Write Cycle Time 10 — Address Valid to End of Write 7 — Chip Select Low to End of Write 7 — Address Set-up Time 0 — Address Hold from End of Write 7 — Address Hold from End of Write 5 — Write Pulse Width 7 — Data Valid to End of Write 5 — Data Hold Time 0 — Write Enable High to Output in Low-Z 3 — Write Enable High to Output in Low-Z 3 — Write Enable High to Output in Low-Z 3 —	Read Cycle Time					

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Timing Waveform of Read Cycle No. 1(1,2,3)



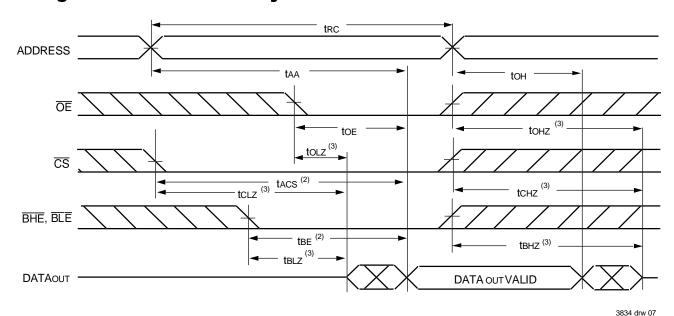
NOTES:

- 1. WE is HIGH for Read Cycle.
- Device is continuously selected, $\overline{\text{CS}}$ is LOW.
- \overline{OE} , \overline{BHE} , and \overline{BLE} are LOW.

^{1.} This parameter is guaranteed with the AC Load (Figure 2) by device characterization, but is not production tested.

^{2.} 0° C to +70°C temperature range only.

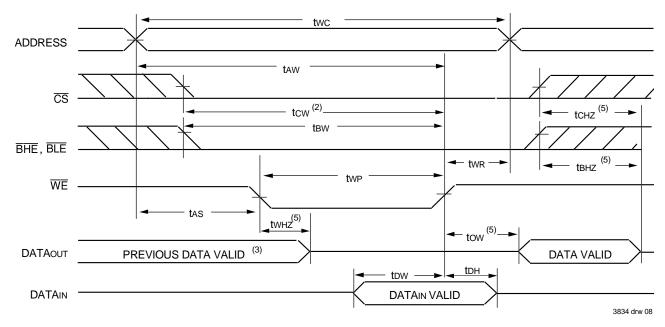
Timing Waveform of Read Cycle No. 2(1)



NOTES:

- 1. WE is HIGH for Read Cycle.
- 2. Address must be valid prior to or coincident with the later of \overline{CS} , \overline{BHE} , or \overline{BLE} transition LOW; otherwise tAA is the limiting parameter.
- 3. Transition is measured ±200mV from steady state.

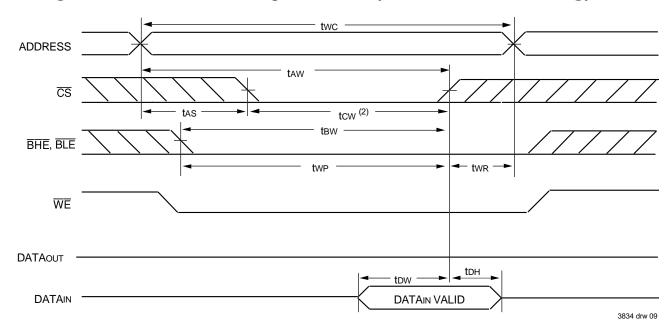
Timing Waveform of Write Cycle No. 1 (WE Controlled Timing)(1,2,4)



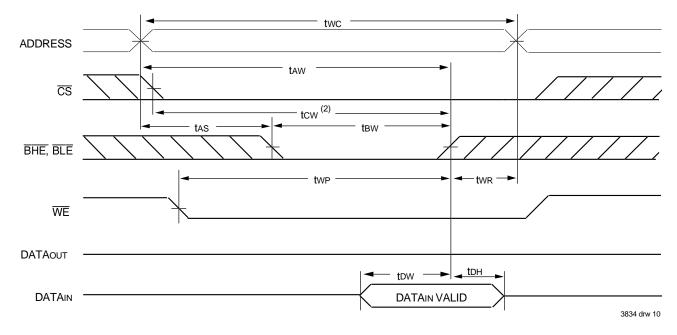
NOTES:

- 1. A write occurs during the overlap of a LOW \overline{CS} , LOW \overline{BHE} or \overline{BLE} , and a LOW \overline{WE} .
- 2. \overline{OE} is continuously HIGH. If during a \overline{WE} controlled write cycle \overline{OE} is LOW, twp must be greater than or equal to twHz+tow to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If \overline{OE} is HIGH during a \overline{WE} controlled write cycle, this requirement does not apply and the minimum write pulse is as short as the specified twp.
- 3. During this period, I/O pins are in the output state, and input signals must not be applied.
- 4. If the CSLOW or BHE and BLE LOW transition occurs simultaneously with or after the WE LOW transition, the outputs remain in a high-impedance state.
- 5. Transition is measured ±200mV from steady state.

Timing Waveform of Write Cycle No. 2 (CS Controlled Timing)(1,4)



Timing Waveform of Write Cycle No. 3 (BHE, BLE Controlled Timing)(1,4)



NOTES:

- 1. A write occurs during the overlap of a LOW \overline{CS} , LOW \overline{BHE} or \overline{BLE} , and a LOW \overline{WE} .
- 2. \overline{OE} is continuously \overline{HIGH} . If during a \overline{WE} controlled write cycle \overline{OE} is LOW, twp must be greater than or equal to twHz+tbw to allow the I/O drivers to turn off and data to be placed on the bus for the required tbw. If \overline{OE} is HIGH during a \overline{WE} controlled write cycle, this requirement does not apply and the minimum write pulse is as short as the specified twp.
- 3. During this period, I/O pins are in the output state, and input signals must not be applied.
- 4. If the \overline{CS} LOW or \overline{BHE} and \overline{BLE} LOW transition occurs simultaneously with or after the \overline{WE} LOW transition, the outputs remain in a high-impedance state.
- 5. Transition is measured ±200mV from steady state.